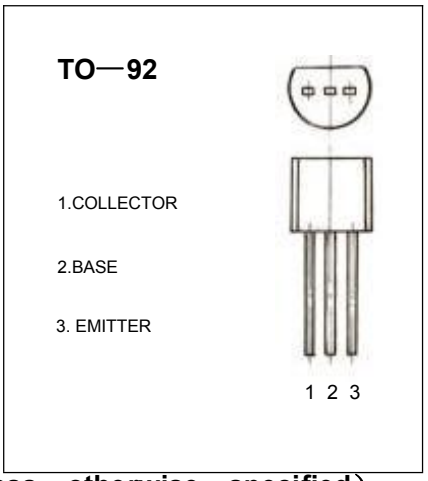
TO-92 Plastic-Encapsulate Transistors

2N6426 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: 1.2 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=10mA，I_B=0	40			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=10μA，I_C=0	12			V
Collector cut-off current	I_{CBO}	V_{CB}=30 V, I_E=0			50	μA
Collector cut-off current	I_{EBO}	V_{EB}=25 V，I_B=0			1.0	μA
Emitter cut-off current	H_{FE}（1）	V_{CE}=10V, I_C=0mA			50	μA
DC current gain	H_{FE}（2）	V_{CE}=5V, I_C=10mA	20K		200K	
DC current gain	H_{FE}（3）	V_{CE}=5V, I_C=100mA	30K		300K	
DC current gain	H_{FE}（4）	V_{CE}=5V, I_C=500mA	20K		200K	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=50mA, I_B=0.5mA			1.5	V
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B=0.5mA			1.2	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500mA, I_B=0.5mA			2.0	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=50mA			1.75	V

CLASSIFICATION OF HFE

Rank	1	2	3
Range	20K-100K	100K-200K	200K-300K